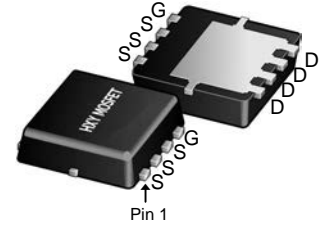




### Description

The SIS410DN-T1-GE3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN3X3-8L

### General Features

$V_{DS} = 20V$   $I_D = 60A$

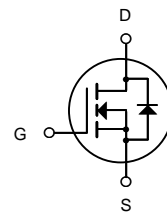
$R_{DS(ON)} < 5m\Omega$  @  $V_{GS}=4.5V$

### Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SIS410DN-T1-GE3	DFN3X3-8L	HXY MOSFET	5000

### Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	60	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	33	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	220	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	46	mJ
$I_{AS}$	Avalanche Current	25	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	15	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	4.5	°C/W



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.7	1.1	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A	-	4.0	5	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =20A	-	6.0	9	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f = 1.0MHz	-	2500	-	pF
C <sub>oss</sub>	Output Capacitance		-	407	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	386	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =30A, V <sub>GS</sub> =4.5V	-	32	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	3	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	11	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =10V, I <sub>D</sub> =30A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	17	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	49	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	74	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	26	-	ns
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> =30A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

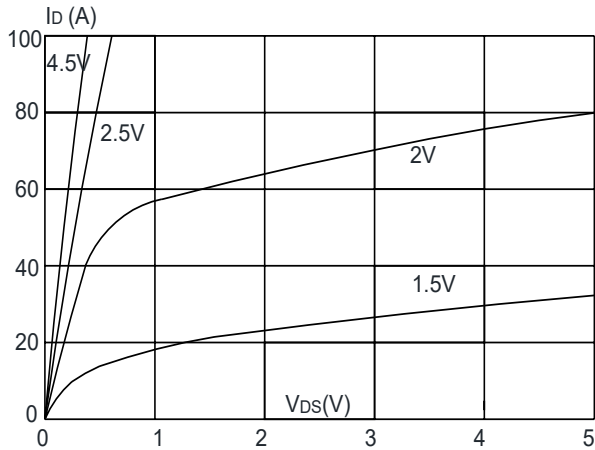
2. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=10V, V<sub>G</sub>=4.5V, L=0.5mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=15A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

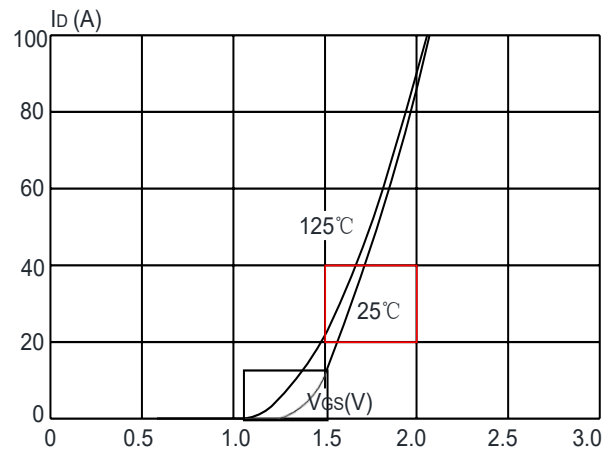


## Typical Performance Characteristics

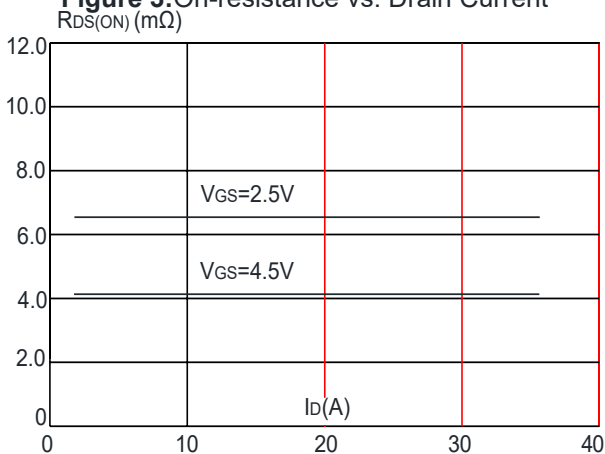
**Figure 1:** Output Characteristics



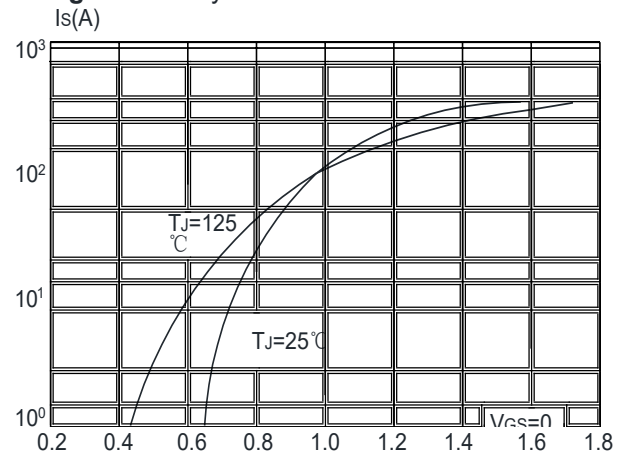
**Figure 2:** Typical Transfer Characteristics



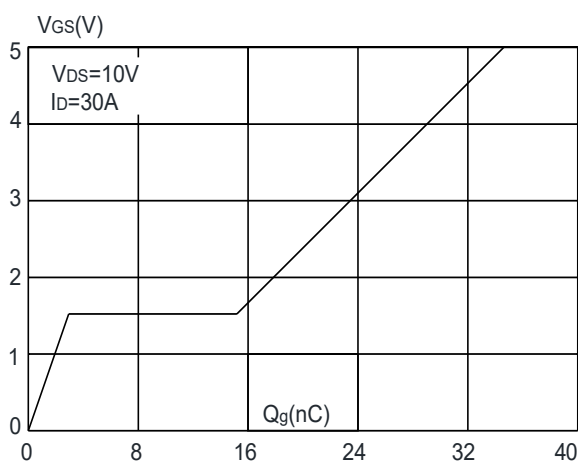
**Figure 3:** On-resistance vs. Drain Current



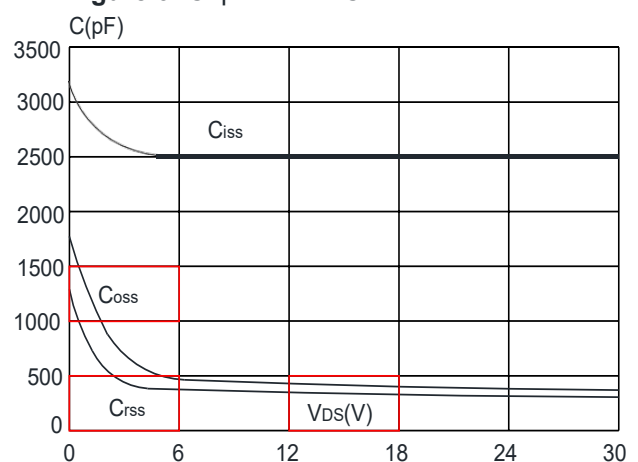
**Figure 4:** Body Diode Characteristics



**Figure 5:** Gate Charge Characteristics

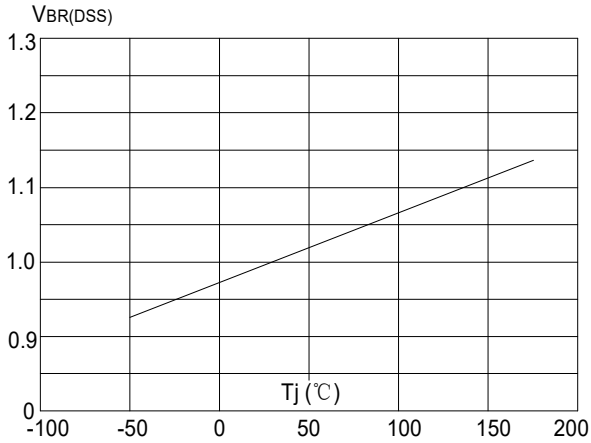


**Figure 6:** Capacitance Characteristics

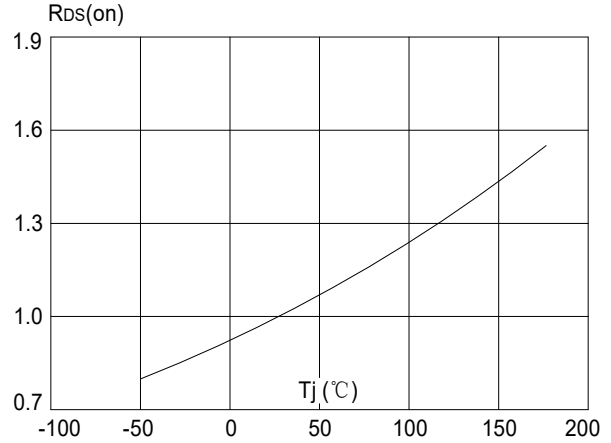




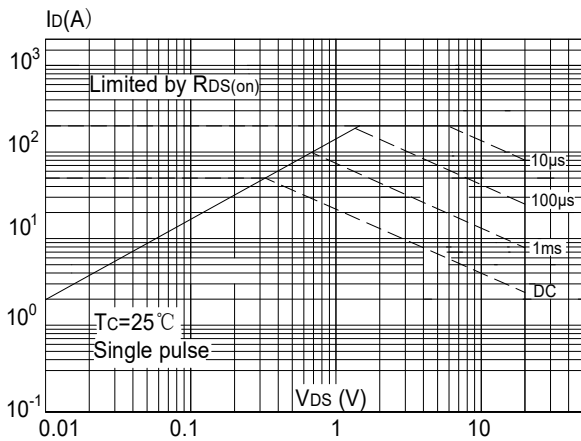
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



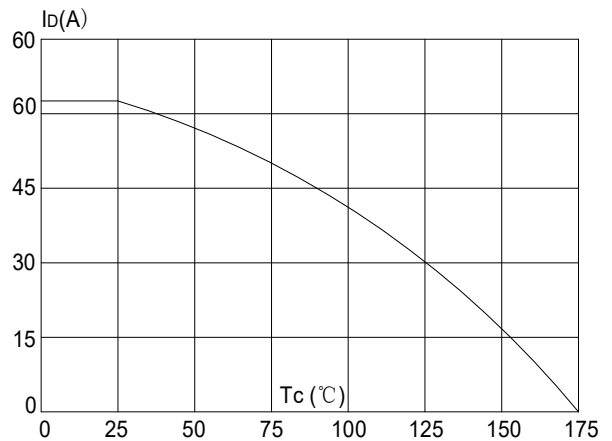
**Figure 8:** Normalized on Resistance vs. Junction Temperature



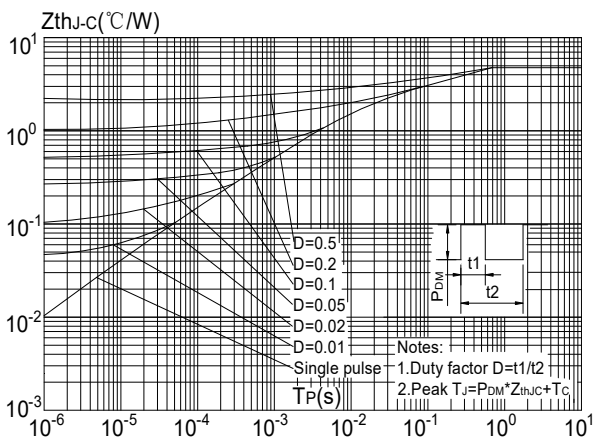
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





### DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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